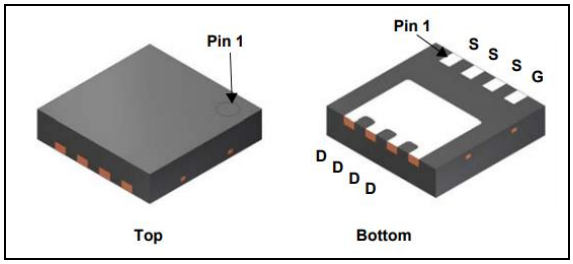
N-Channel 100 V MOSFET

Product summary

V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
100	18 @ V_{GS} = 10V	40 (1)

DFN3X3-8L

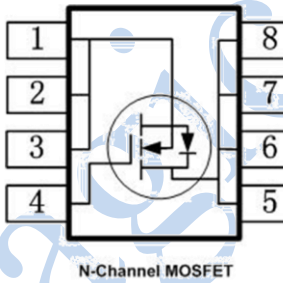


Features

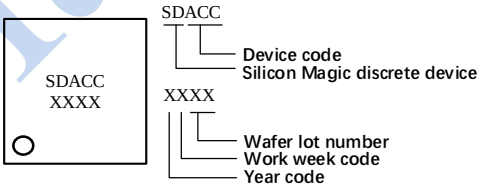
- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- Motor drives



Pb-free
RoHS COMPLIANT
HALOGEN FREE



Package and ordering information

Ordering code	Package	Device code
SDN10K018S2Z	DFN3X3-8L	ACC

1. Maximum ratings

Absolute maximum ratings (T_A = 25℃ unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current(1)	T_C=25℃	I_D	40	A
	T_C=100℃		25	
	T_A=25℃ (4)		8	
Pulsed drain current(2)		$I_{D,pulse}$	160	
Avalanche energy, single pulse(3)		E_{AS}	88	mJ
Power dissipation	T_C=25℃	P_D	52	W
	T_A=25℃ (4)		2.3	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 150	℃

2. Thermal resistance ratings

Thermal resistance ratings				
Parameter		**Symbol**	**Max.**	**Unit**
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	2.4	℃/W
Thermal resistance, junction-to-ambient (4)	Steady state	$R_{\theta JA}$	53	

3. Electrical Characteristics

Electrical characteristics						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static parameter						
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	100			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.2	1.9	2.6	V
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	μA
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 8 A		13	18	mΩ
Forward transconductance (5)	g_{fs}	V_{DS} = 5 V, I_D = 8 A		47		S
Gate resistance	R_g			1	2	Ω
Dynamic(5)						
Total gate charge	Q_g	V_{DS} = 50 V, I_D = 8 A, V_{GS} = 10 V		26	37	nC
Gate-source charge	Q_{gs}			4	6	
Gate-drain charge	Q_{gd}			7.5	11	
Turn-on delay time	$t_{d(on)}$	V_{DS} = 50 V, I_D = 8 A, V_{GS} = 10 V, R_{GEN} = 6Ω		14	28	ns
Rise time	t_r			5.5	11	
Turn-off delay time	$t_{d(off)}$			40	80	
Fall time	t_f			12.5	25	
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		1195	1675	pF
Output capacitance	C_{oss}			215	300	
Reverse transfer capacitance	C_{rss}			8	16	
Reverse Diode Characteristics (5)						
Diode forward voltage	V_{SD}	V_{GS} = 0 V, I_F = 8 A		0.8	1.1	V
Reverse recovery time	t_{rr}	V_{DS} = 50 V,I_F = 8 A, di/dt = 100 A/μs		38	69	ns
Reverse recovery charge	Q_{rr}			71	128	nC

Notes

(1) Limited by maximum junction temperature.

(2) Pulse width limited by maximum junction temperature.

(3) V_{DS} = 75 V, V_{GS} = 10 V, L = 0.3 mH.

(4) $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.

(5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

Fig.1 Typ. transfer characteristics

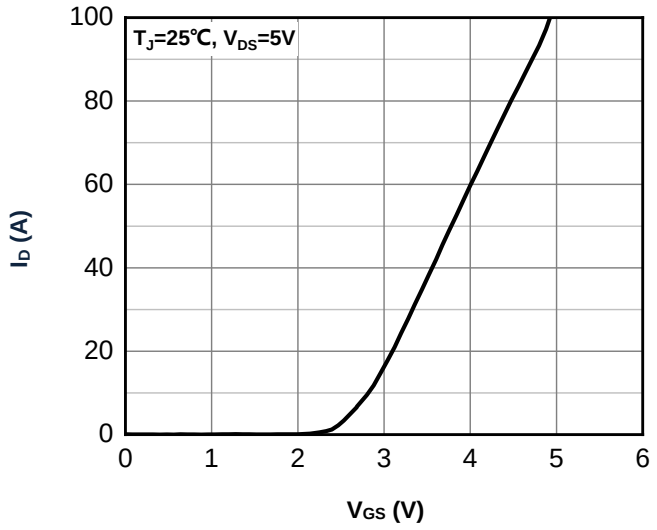


Fig.2 Typ. output characteristics

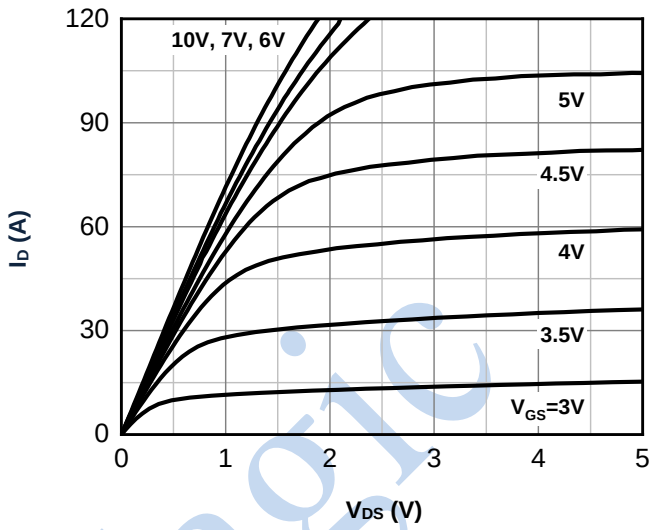


Fig.3 Normalized on-resistance vs drain current

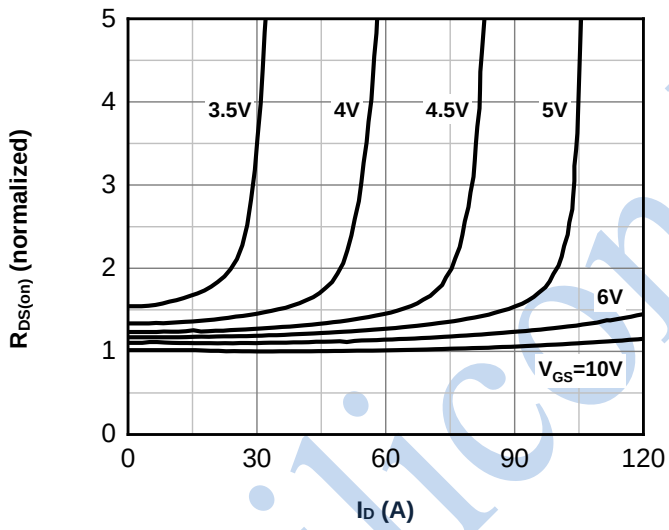


Fig.4 Typ. on-resistance vs gate-source voltage

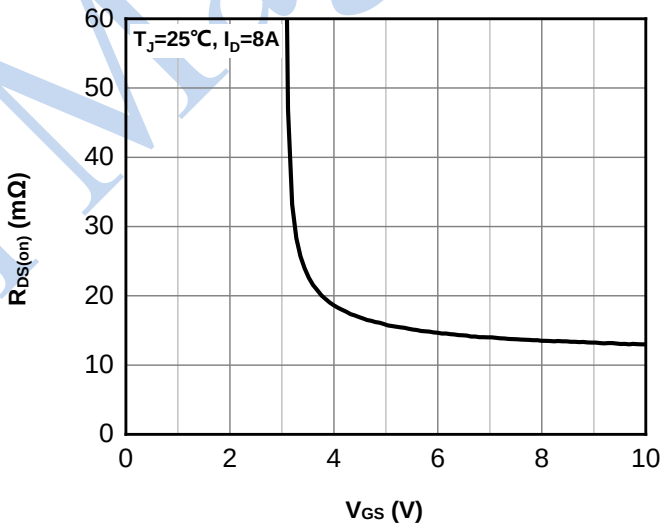


Fig.5 Normalized on-resistance vs junction temperature

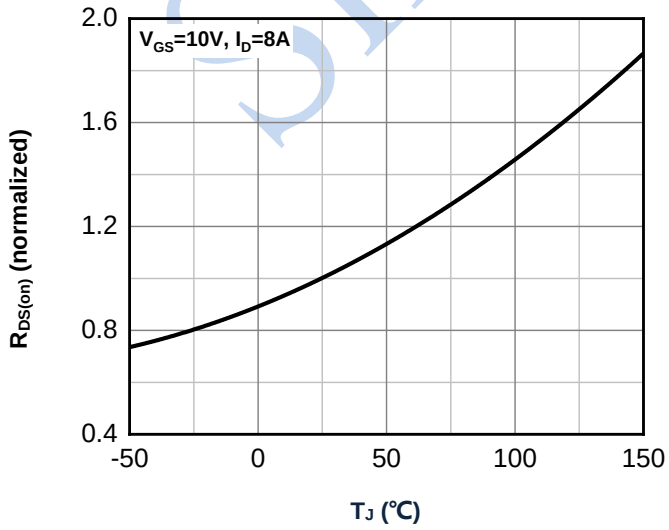


Fig.6 Typ. gate charge

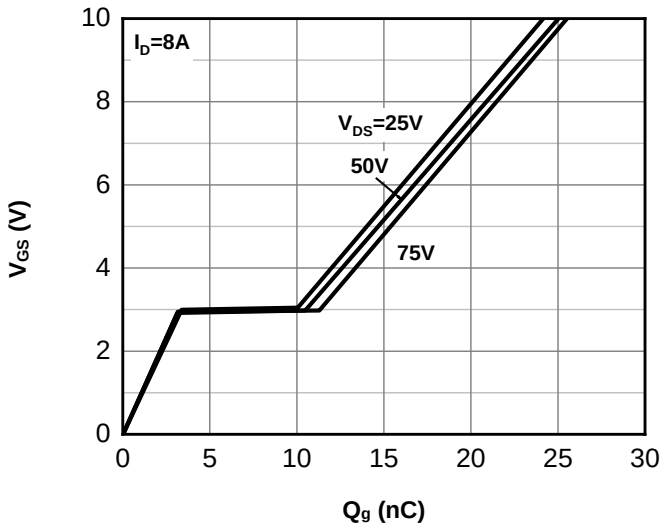


Fig.7 Typ. forward characteristics of body diode

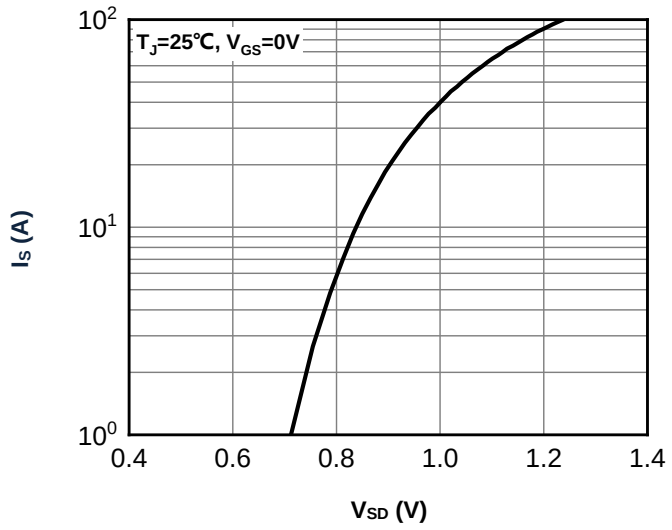


Fig.8 Safe operating area

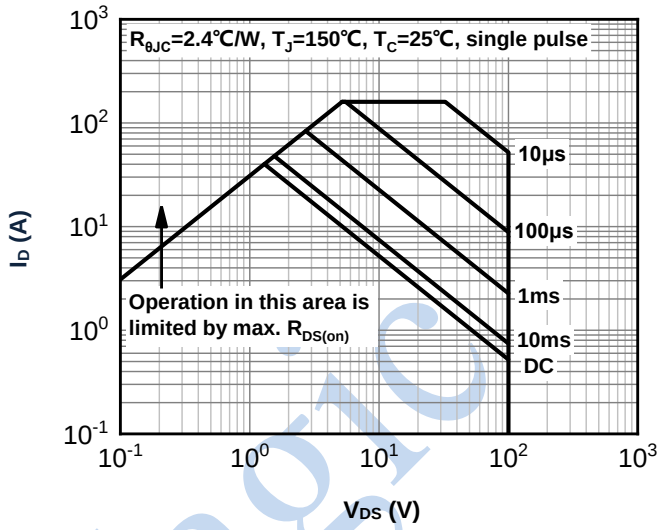


Fig.9 Typ. Capacitance

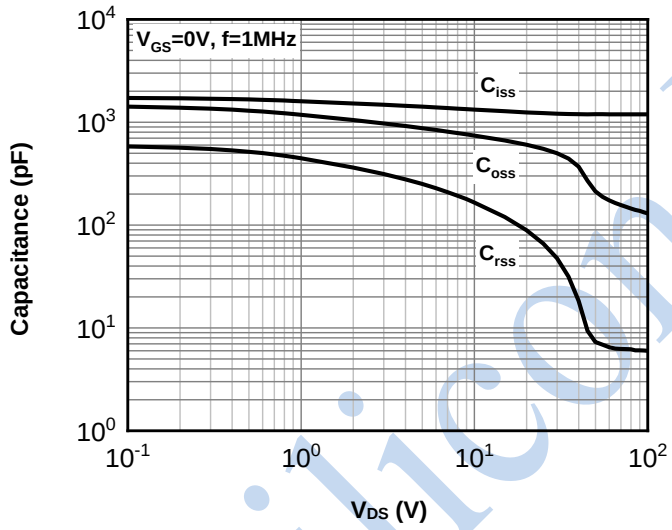


Fig.10 Single pulse maximum power dissipation

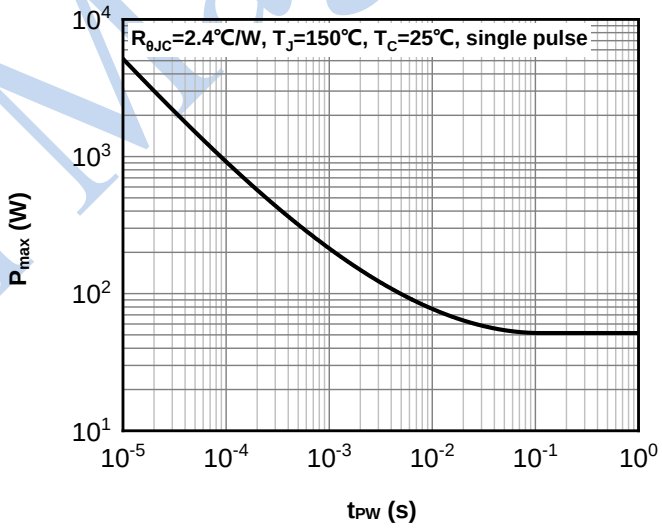


Fig.11 Max. power dissipation vs case temperature

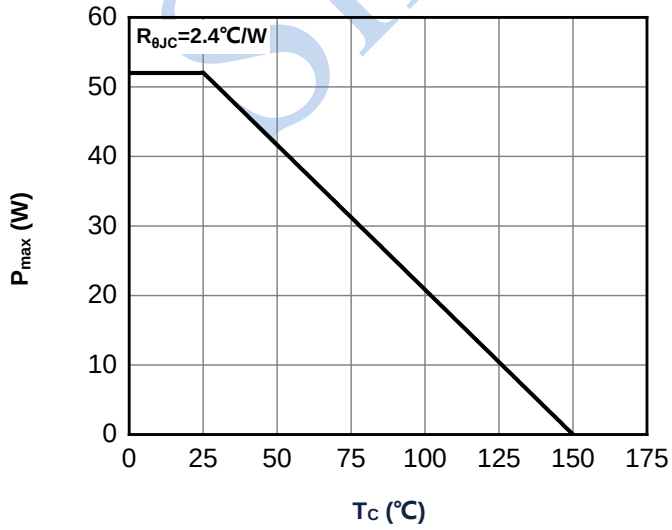


Fig.12 Max. continuous drain current vs case temperature

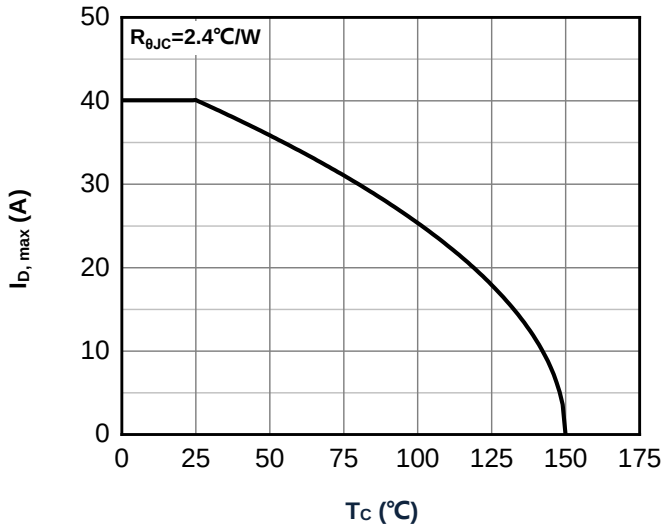
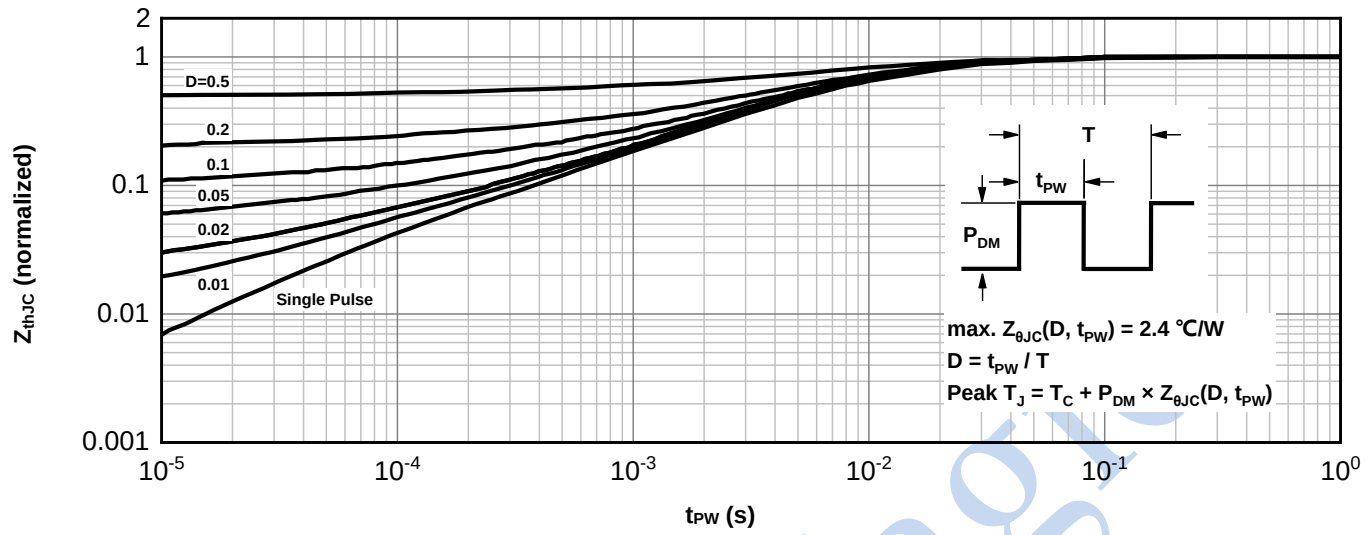
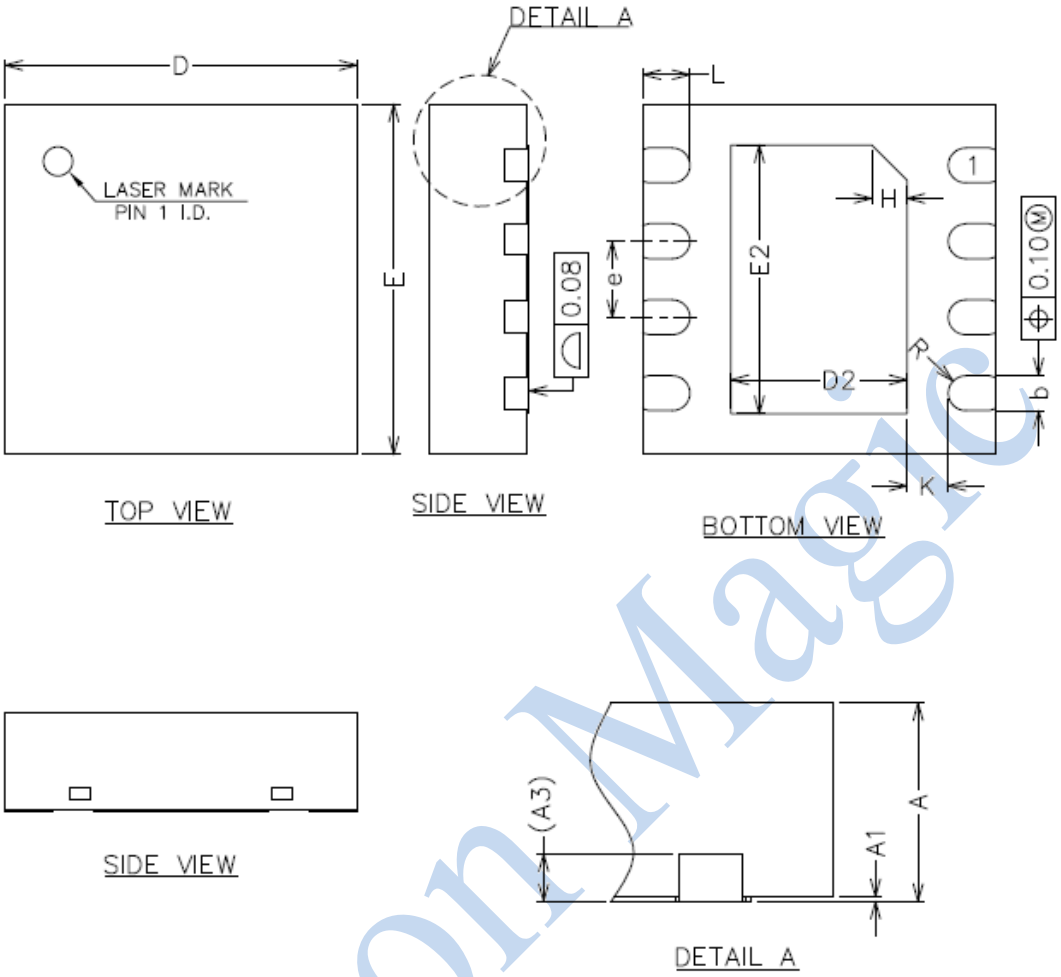


Fig.13 Normalized transient thermal impedance from junction to case



5. Package outline dimensions



COMMON DIMENSIONS

(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
A3		0.20REF	
b	0.25	0.30	0.35
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.40	1.50	1.60
E2	2.20	2.30	2.40
e	0.55	0.65	0.75
H		0.30REF	
K	0.25	0.35	0.45
L	0.35	0.40	0.45
R	0.13	——	——

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